

Bipolar Transistor

-50 V, -10 A, Low V_{CE}(sat), PNP TO-220F-3FS

2SA2222SG

Features

- Adoption of MBIT Process
- Large Current Capacity ($I_C = -10 \text{ A}$)
- Low Collector to Emitter Saturation Voltage (V_{CE}(sat) = −250 mV (Typ.))
- High-speed Switching (tf = 22 ns (Typ.))
- This is a Pb-Free Device

Applications

• Relay Drivers, Lamp Drivers, Motor Drivers

SPECIFICATIONS ABSOLUTE MAXIMUM RATINGS at Ta = 25°C

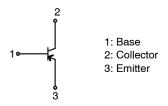
Parameter		Symbol	Value	Unit
Collector-to-Base Voltage		V_{CBO}	-50	V
Collector-to-Emitter Voltage		V_{CEO}	-50	V
Emitter-to-Base Voltage		V _{EBO}	-6	V
Collector Current		Ic	-10	Α
Collector Current (Pulse)		I _{CP}	-13	Α
Base Current		Ι _Β	-2	Α
Collector Dissipation	Tc = 25°C, $P_T \le 1s$	P _C	25	W
Junction Temperature		T_J	150	∘C
Storage Temperature		T _{STG}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



TO-220F-3FS CASE 221AM

ELECTRICAL CONNECTION



MARKING DIAGRAM



ORDERING INFORMATION

Device	Package	Shipping
2SA2222SG	TO-220F-3FS (Pb-Free)	50 Units/Tube

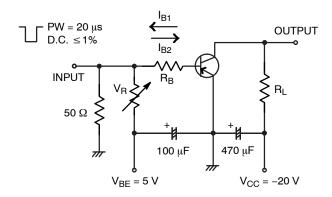
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ELECTRICAL CHARACTERISTICS at Ta = 25°C

			Ratings			
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector Cutoff Current	I _{CBO}	$V_{CB} = -40 \text{ V}, I_E = 0 \text{ A}$			-10	μΑ
Emitter Cutoff Current	I _{EBO}	$V_{EB} = -4V$, $I_C = 0$ A			-10	μΑ
DC Current Gain	h _{FE}	$V_{CE} = -2 \text{ V}, I_{C} = -270 \text{ mA}$	150		450	
Gain-Bandwidth Product	f _T	$V_{CE} = -10 \text{ V}, I_{C} = -1 \text{ A}$		230		MHz
Output Capacitance	Cob	V _{CB} = -10 V, f = 1 MHz		115		pF
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)	$I_C = -6 \text{ A}, I_B = -300 \text{ mA}$		-250	-500	mV
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	$I_C = -6 \text{ A}, I_B = -300 \text{ mA}$			-1.2	V
Collector-to-Base Breakdown Voltage	V _{(BR)CBO}	$I_C = -100 \mu A, I_E = 0 A$	-50			V
Collector-to-Emitter Breakdown Voltage	V _{(BR)CEO}	$I_C = -1$ mA, $R_{BE} = \infty$	-50			V
Emitter-to-Base Breakdown Voltage	V _{(BR)EBO}	$I_E = -100 \mu A, I_C = 0 A$	-6			V
Turn-On Time	t _{on}	See specified Test Circuit		40		ns
Storage Time	t _{stg}			240		ns
Fall Time	t _f			22		ns

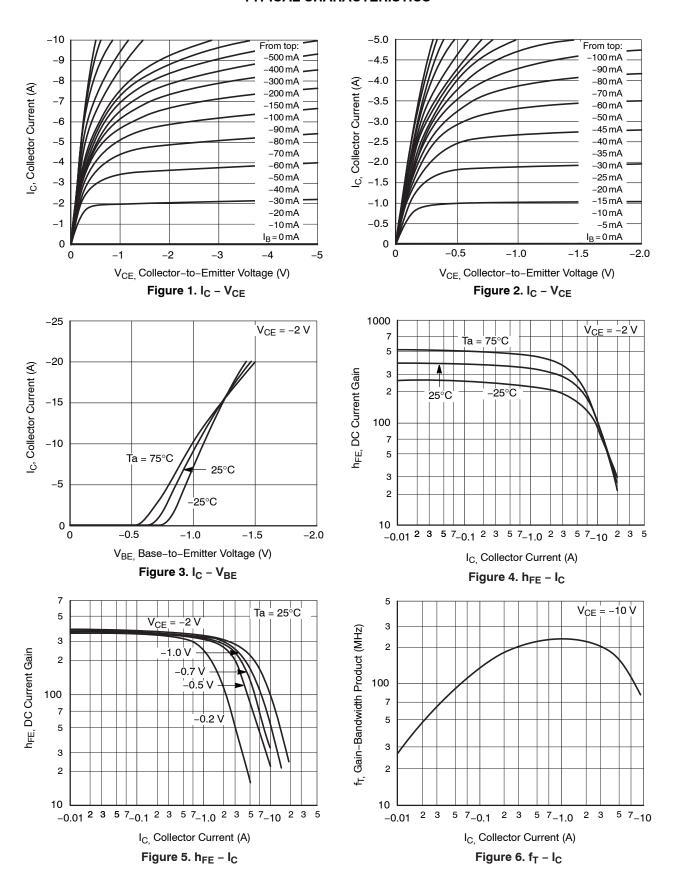
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit



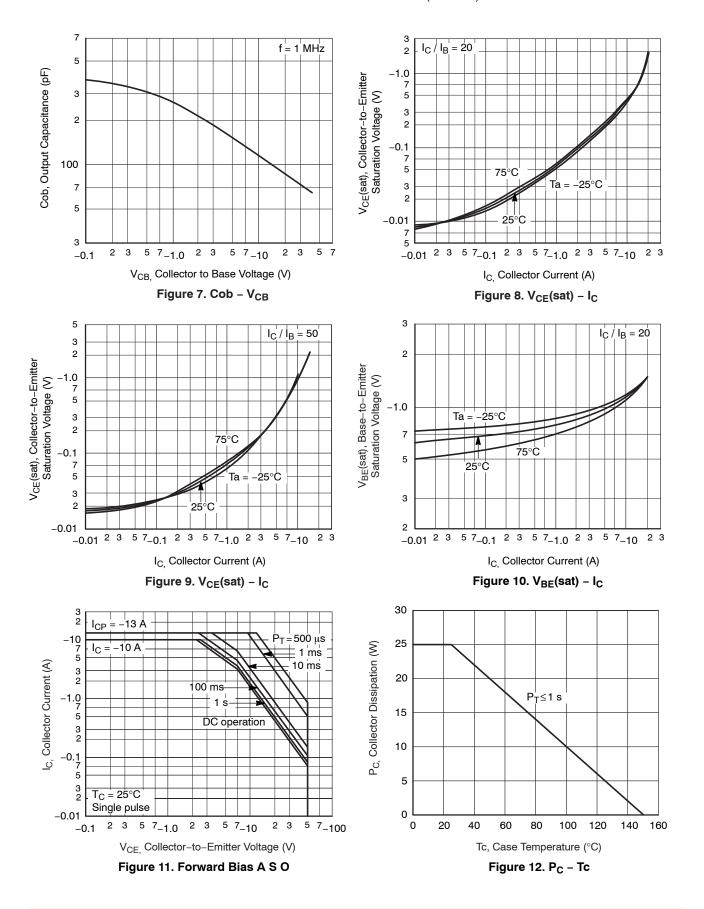
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TYPICAL CHARACTERISTICS



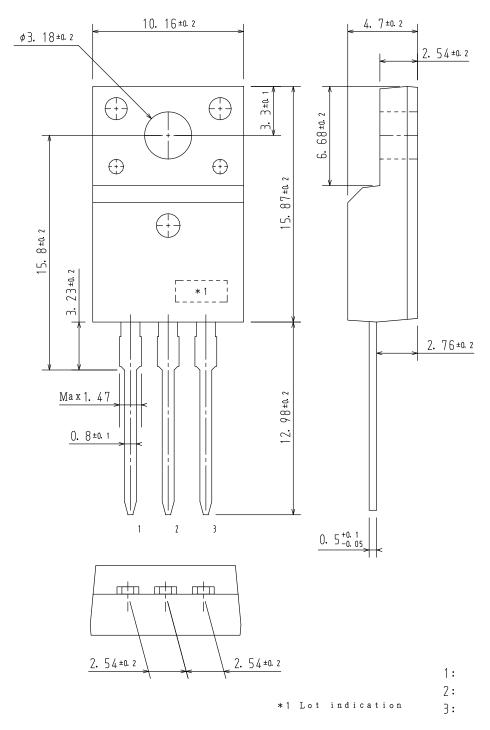
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TYPICAL CHARACTERISTICS (continued)



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